

## MAREA P2 Bi-Sb LAYERS AND WIRES FOR MAGNETO- THERMOELECTRIC APPLICATIONS

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Thermoelectric energy conversion efficiency is defined as  $ZT = S^2\sigma/\chi T$ , where  $S$  is the Seebeck coefficient,  $\sigma$  is the electrical conductivity,  $\chi$  is the thermal conductivity, and  $T$  is the absolute temperature.

This study is aimed at increasing the thermoelectric figure of merit  $ZT$  to maximize the power factor and minimize the thermal conductivity.

Since undoped Bi–12at%Sb alloys are of  $n$ -type, the possibility of obtaining  $p$ -type Bi–Sb alloys (bulk samples and layers) with a high figure of merit by the addition of acceptor impurities and the application of a transverse magnetic field has been explored.

The mechanical exfoliation method was used to obtain  $\text{Bi}_{1-x}\text{Sb}_x$  layers and the liquid-phase casting method (Ulitsky–Taylor) was used to prepare wires [1].

In this paper, we present the results of measurements of transport effects in undoped and doped Bi–12at%Sb–0.001at%Pb alloy bulk samples, single-crystal layers, and glass-insulated wires. The measurements included the electrical resistivity, Seebeck coefficient  $S$ , and the Nernst coefficient as a function of crystallographic direction, temperature, and magnetic field direction.

The values and temperature dependence of power factor  $\alpha^2\sigma$ , which were calculated from experimental data in a transverse magnetic field, showed a considerable increase in this parameter in the wires and layers compared with the bulk samples in a magnetic field of 0.3 T [2, 3]. A combination of the Peltier and magneto-Peltier effects in Bi–Sb layers and wires provides a stronger cooling both from room temperature and from 100 K than the cooling in bulk alloys of the same composition.

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